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With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

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Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



HEXFET® Power MOSFET

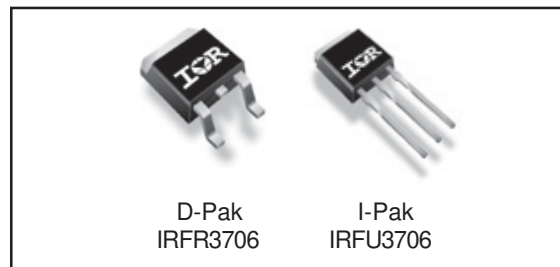
**Applications**

- High Frequency Isolated DC-DC Converters with Synchronous Rectification for Telecom and Industrial Use
- High Frequency Buck Converters for Computer Processor Power

<b>V<sub>DSS</sub></b>	<b>R<sub>DS(on)</sub> max</b>	<b>I<sub>D</sub></b>
<b>20V</b>	<b>9.0mΩ</b>	<b>75A<sup>④</sup></b>

**Benefits**

- Ultra-Low Gate Impedance
- Very Low R<sub>DS(on)</sub> at 4.5V V<sub>GS</sub>
- Fully Characterized Avalanche Voltage and Current



**Absolute Maximum Ratings**

Symbol	Parameter	Max.	Units
V <sub>DS</sub>	Drain-Source Voltage	20	V
V <sub>GS</sub>	Gate-to-Source Voltage	± 12	V
I <sub>D</sub> @ T <sub>C</sub> = 25°C	Continuous Drain Current, V <sub>GS</sub> @ 10V	75 <sup>④</sup>	A
I <sub>D</sub> @ T <sub>C</sub> = 100°C	Continuous Drain Current, V <sub>GS</sub> @ 10V	53 <sup>④</sup>	
I <sub>DM</sub>	Pulsed Drain Current <sup>①</sup>	280	
P <sub>D</sub> @ T <sub>C</sub> = 25°C	Maximum Power Dissipation <sup>③</sup>	88	W
P <sub>D</sub> @ T <sub>C</sub> = 100°C	Maximum Power Dissipation <sup>③</sup>	44	W
	Linear Derating Factor	0.59	mW/°C
T <sub>J</sub> , T <sub>STG</sub>	Junction and Storage Temperature Range	-55 to + 175	°C

**Thermal Resistance**

	Parameter	Typ.	Max.	Units
R <sub>θJC</sub>	Junction-to-Case <sup>⑤</sup>	—	1.7	°C/W
R <sub>θJA</sub>	Junction-to-Ambient (PCB mount)* <sup>⑤</sup>	—	50	
R <sub>θJA</sub>	Junction-to-Ambient <sup>⑤</sup>	—	110	

\* When mounted on 1" square PCB (FR-4 or G-10 Material) .  
For recommended footprint and soldering techniques refer to application note #AN-994

Notes ① through ⑤ are on page 10

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## Static @ T<sub>J</sub> = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
V <sub>(BR)DSS</sub>	Drain-to-Source Breakdown Voltage	20	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
ΔV <sub>(BR)DSS</sub> /ΔT <sub>J</sub>	Breakdown Voltage Temp. Coefficient	—	0.021	—	V/°C	Reference to 25°C, I <sub>D</sub> = 1mA
R <sub>DS(on)</sub>	Static Drain-to-Source On-Resistance	—	6.9	9.0	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 15A ③
		—	8.1	11		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 12A ③
		—	11.5	23		V <sub>GS</sub> = 2.8V, I <sub>D</sub> = 7.5A ③
V <sub>GS(th)</sub>	Gate Threshold Voltage	0.6	—	2.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
I <sub>DSS</sub>	Drain-to-Source Leakage Current	—	—	20	μA	V <sub>DS</sub> = 16V, V <sub>GS</sub> = 0V
		—	—	100		V <sub>DS</sub> = 16V, V <sub>GS</sub> = 0V, T <sub>J</sub> = 125°C
I <sub>GSS</sub>	Gate-to-Source Forward Leakage	—	—	200	nA	V <sub>GS</sub> = 12V
	Gate-to-Source Reverse Leakage	—	—	-200		V <sub>GS</sub> = -12V

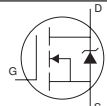
## Dynamic @ T<sub>J</sub> = 25°C (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
g <sub>fs</sub>	Forward Transconductance	53	—	—	S	V <sub>DS</sub> = 16V, I <sub>D</sub> = 57A
Q <sub>g</sub>	Total Gate Charge	—	23	35	nC	I <sub>D</sub> = 28A
Q <sub>gs</sub>	Gate-to-Source Charge	—	8.0	12		V <sub>DS</sub> = 10V
Q <sub>gd</sub>	Gate-to-Drain ("Miller") Charge	—	5.5	8.3		V <sub>GS</sub> = 4.5V ③
Q <sub>oss</sub>	Output Gate Charge	—	16	24		V <sub>GS</sub> = 0V, V <sub>DS</sub> = 10V
R <sub>g</sub>	Gate Resistance	—	1.8	—		Ω
t <sub>d(on)</sub>	Turn-On Delay Time	—	6.8	—	ns	V <sub>DD</sub> = 10V
t <sub>r</sub>	Rise Time	—	87	—		I <sub>D</sub> = 28A
t <sub>d(off)</sub>	Turn-Off Delay Time	—	17	—		R <sub>G</sub> = 1.8Ω
t <sub>f</sub>	Fall Time	—	4.8	—		V <sub>GS</sub> = 4.5V ③
C <sub>iss</sub>	Input Capacitance	—	2410	—	pF	V <sub>GS</sub> = 0V
C <sub>oss</sub>	Output Capacitance	—	1070	—		V <sub>DS</sub> = 10V
C <sub>rss</sub>	Reverse Transfer Capacitance	—	140	—		f = 1.0MHz

## Avalanche Characteristics

Symbol	Parameter	Typ.	Max.	Units
E <sub>AS</sub>	Single Pulse Avalanche Energy②	—	220	mJ
I <sub>AR</sub>	Avalanche Current①	—	28	A

## Diode Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
I <sub>S</sub>	Continuous Source Current (Body Diode)	—	—	75④	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I <sub>SM</sub>	Pulsed Source Current (Body Diode) ①	—	—	280		
V <sub>SD</sub>	Diode Forward Voltage	—	0.88	1.3	V	T <sub>J</sub> = 25°C, I <sub>S</sub> = 36A, V <sub>GS</sub> = 0V ③
		—	0.82	—		T <sub>J</sub> = 125°C, I <sub>S</sub> = 36A, V <sub>GS</sub> = 0V ③
t <sub>rr</sub>	Reverse Recovery Time	—	45	68	ns	T <sub>J</sub> = 25°C, I <sub>F</sub> = 36A, V <sub>R</sub> = 20V
Q <sub>rr</sub>	Reverse Recovery Charge	—	65	98	nC	di/dt = 100A/μs ③
t <sub>rr</sub>	Reverse Recovery Time	—	49	74	ns	T <sub>J</sub> = 125°C, I <sub>F</sub> = 36A, V <sub>R</sub> = 20V
Q <sub>rr</sub>	Reverse Recovery Charge	—	78	120	nC	di/dt = 100A/μs ③

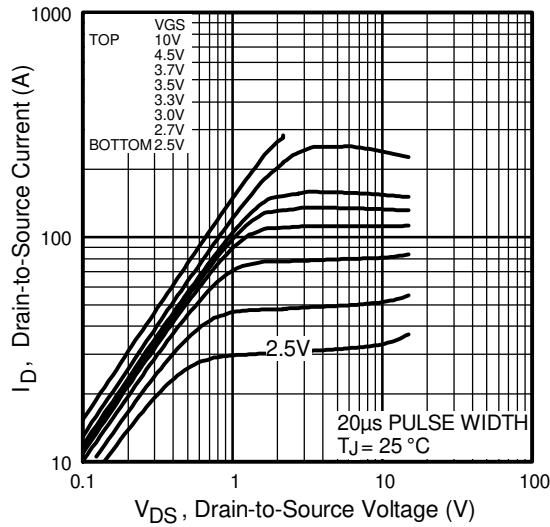


Fig 1. Typical Output Characteristics

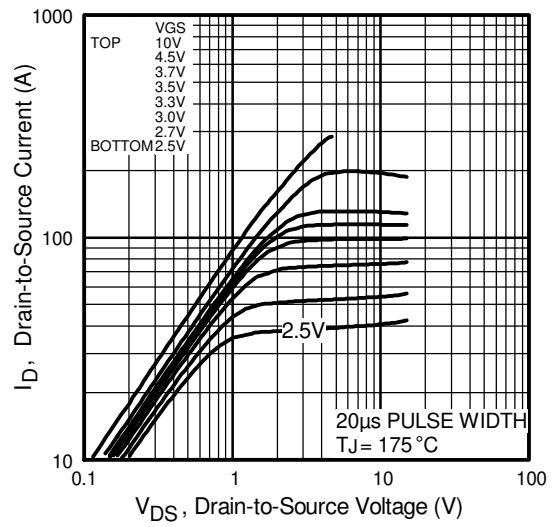


Fig 2. Typical Output Characteristics

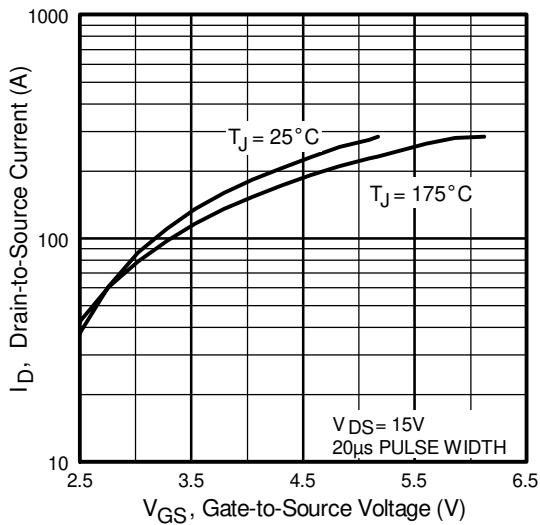


Fig 3. Typical Transfer Characteristics

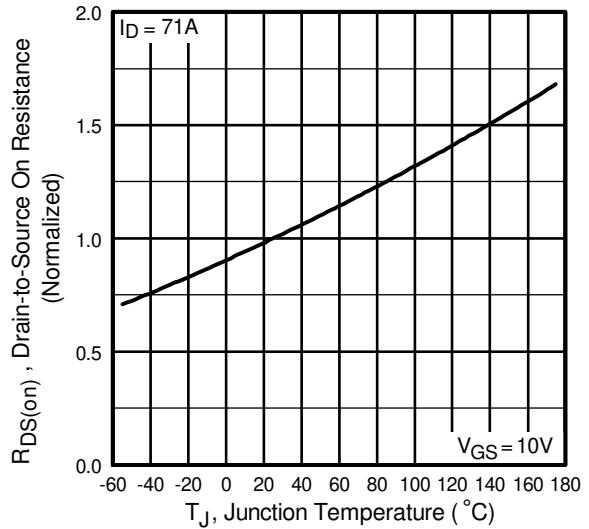
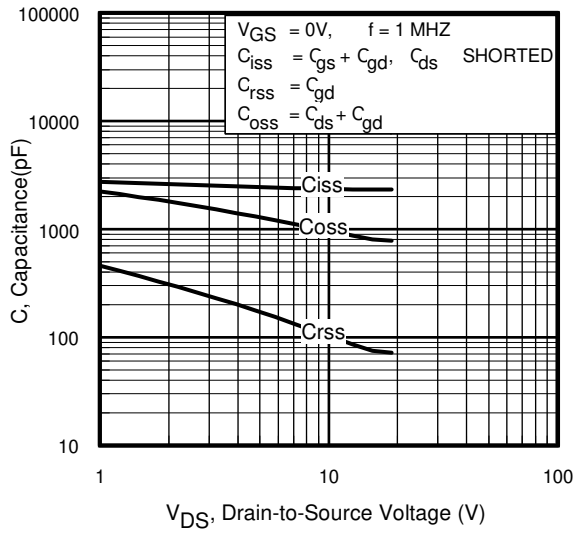
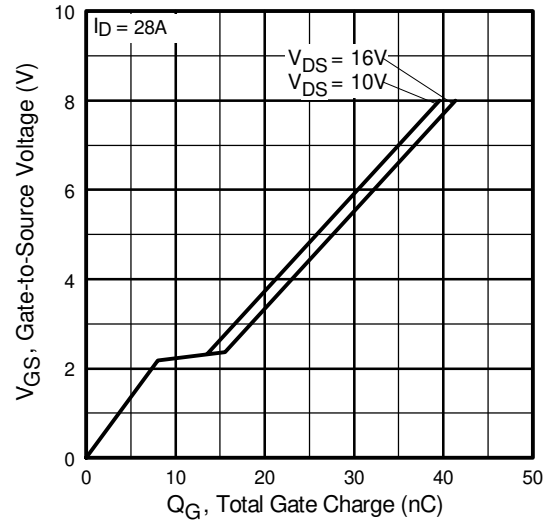


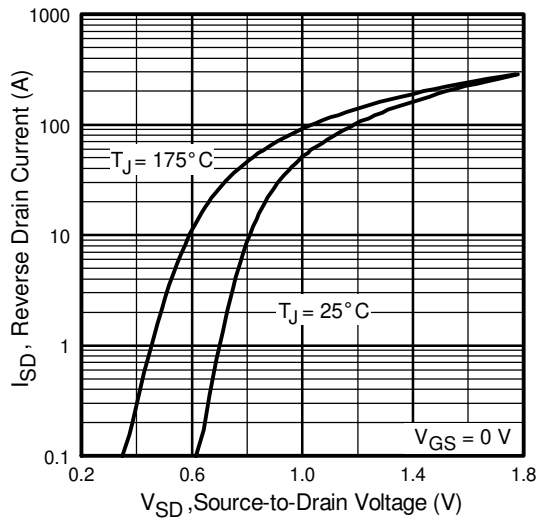
Fig 4. Normalized On-Resistance Vs. Temperature



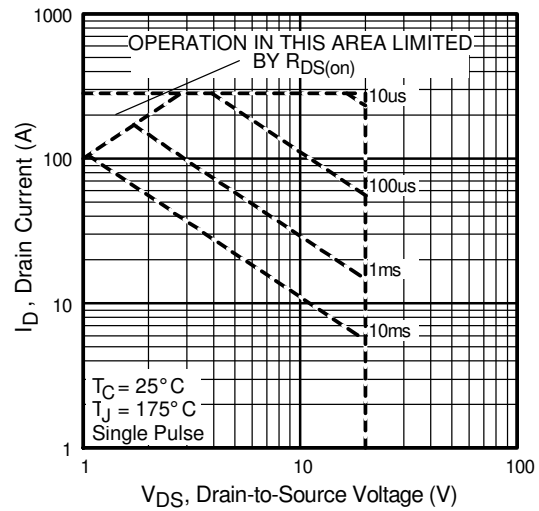
**Fig 5.** Typical Capacitance Vs. Drain-to-Source Voltage



**Fig 6.** Typical Gate Charge Vs. Gate-to-Source Voltage



**Fig 7.** Typical Source-Drain Diode Forward Voltage



**Fig 8.** Maximum Safe Operating Area

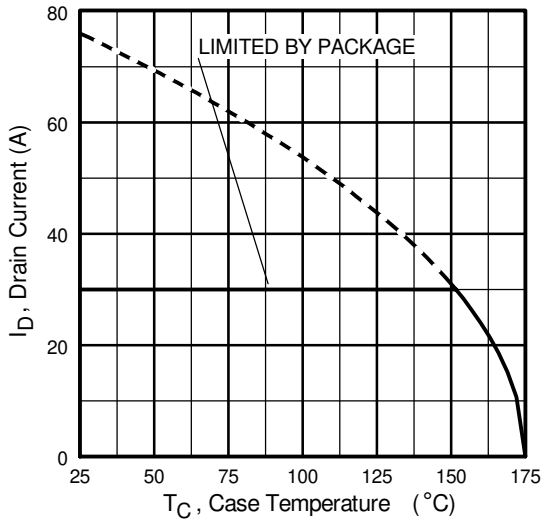


Fig 9. Maximum Drain Current Vs. Case Temperature

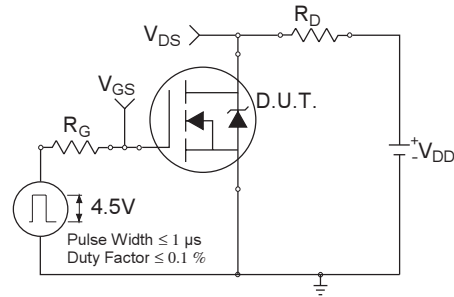


Fig 10a. Switching Time Test Circuit

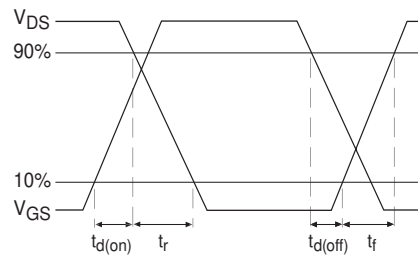


Fig 10b. Switching Time Waveforms

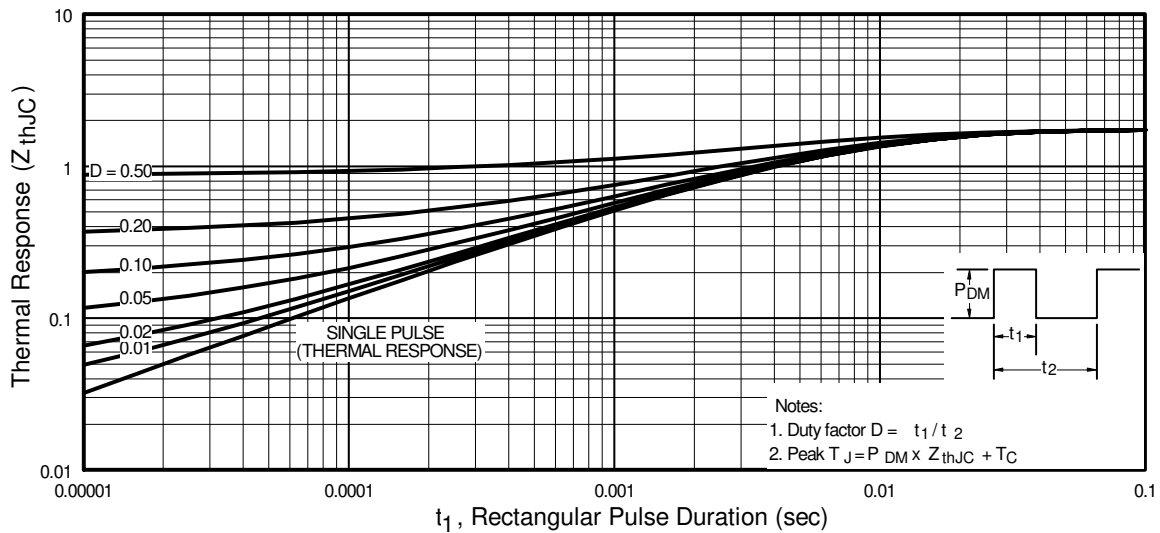
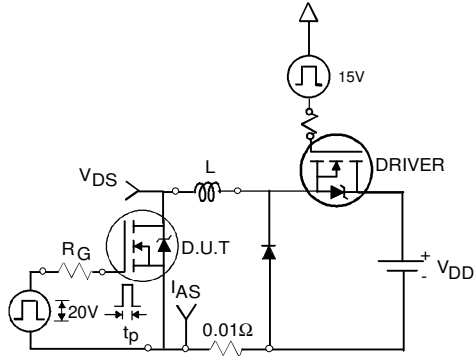


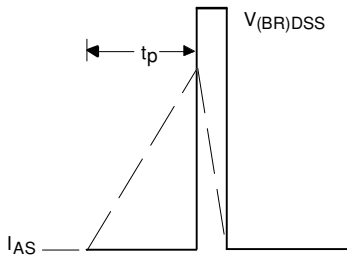
Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

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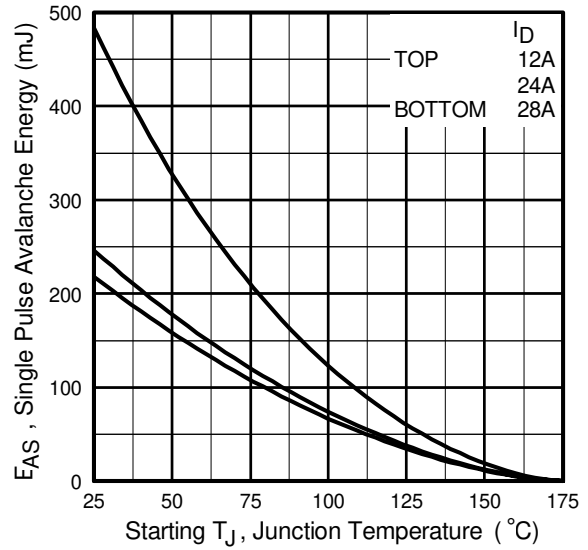
International  
**IR** Rectifier



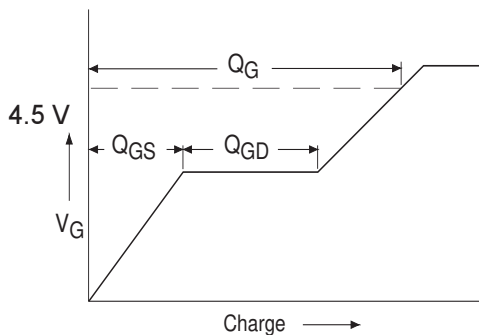
**Fig 12a.** Unclamped Inductive Test Circuit



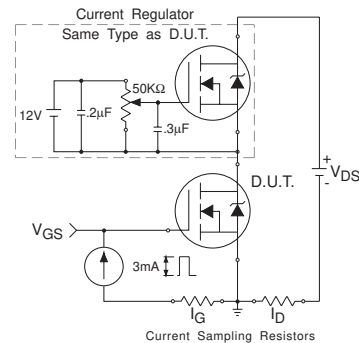
**Fig 12b.** Unclamped Inductive Waveforms



**Fig 12c.** Maximum Avalanche Energy Vs. Drain Current

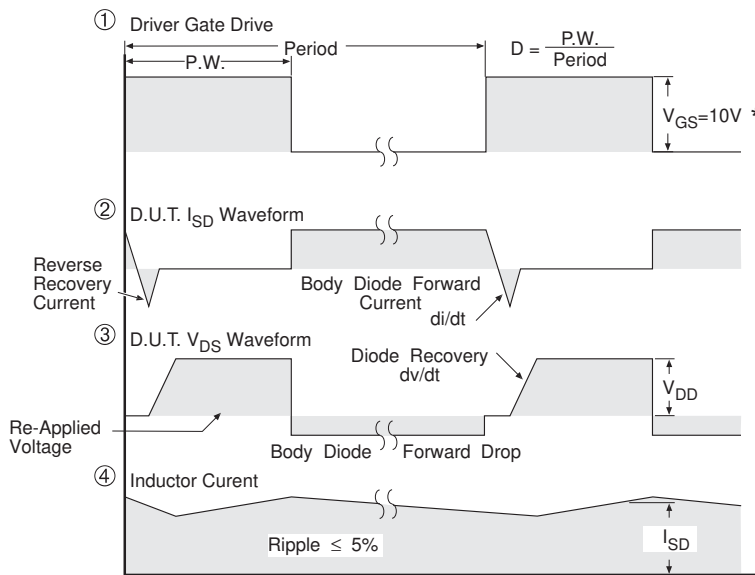
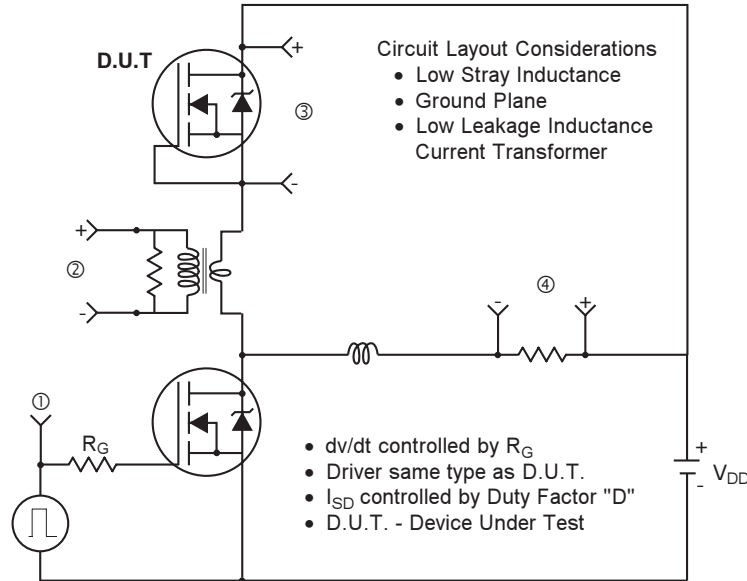


**Fig 13a.** Basic Gate Charge Waveform



**Fig 13b.** Gate Charge Test Circuit

**Peak Diode Recovery dv/dt Test Circuit**



\*  $V_{GS} = 5V$  for Logic Level Devices

**Fig 14.** For N-Channel HEXFET® Power MOSFETs

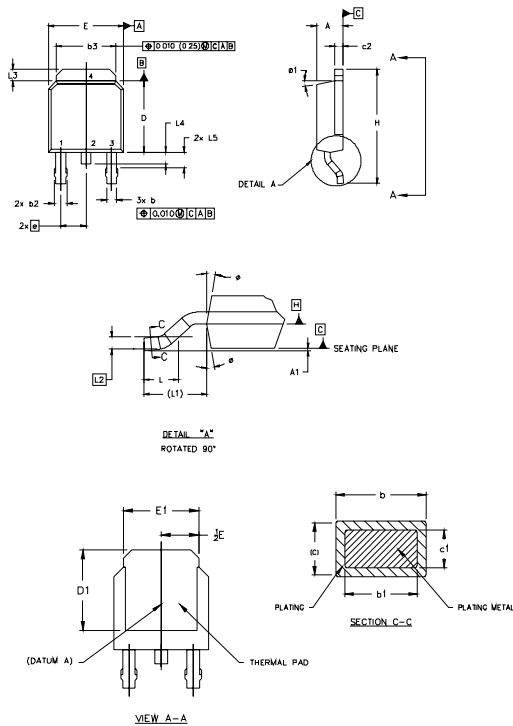


# IRFR/U3706

## D-Pak (TO-252AA) Package Outline

Dimensions are shown in millimeters (inches)

International  
**IR** Rectifier



- NOTES:
- 1.0 DIMENSIONING AND TOLERANCING PER ASME Y14.5 M- 1994.
  - 2.0 DIMENSIONS ARE SHOWN IN INCHES [MILLIMETERS].
  - 3.0 LEAD DIMENSION UNCONTROLLED IN L5
  - 4.0 DIMENSION D1 AND E1 ESTABLISH A MINIMUM MOUNTING SURFACE FOR THERMAL PAD.
  - 5.0 SECTION C-C DIMENSIONS APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN .005 [0.127] AND .010 [0.2540] FROM THE LEAD TIP.
  - 6.0 DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
  - 7.0 OUTLINE CONFORMS TO JEDEC OUTLINE TO-252AA.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	2.18	2.39	.086	.094	
A1		0.13		.005	
b	0.64	0.89	.025	.035	5
b1	0.64	0.79	.025	0.031	5
b2	0.76	1.14	.030	.045	
b3	4.95	5.46	.195	.215	
c	0.46	0.61	.018	.024	5
c1	0.41	0.56	.016	.022	5
c2	.046	0.89	.018	.035	5
D	5.97	6.22	.235	.245	6
D1	5.21	-	.205	-	4
E	6.35	6.73	.250	.265	6
E1	4.32	-	.170	-	4
e	2.29		.090 BSC		
H	9.40	10.41	.370	.410	
L	1.40	1.78	.056	.070	
L1	2.74 REF.		.108 REF.		
L2	0.051 BSC		.020 BSC		
L3	0.89	1.27	.036	.050	
L4		1.02		.040	
L5	1.14	1.52	.045	.060	3
ø	0"	10"	0"	10"	
ø1	0"	15"	0"	15"	

**LEAD ASSIGNMENTS**

- HEXFET  
1.- GATE  
2.- DRAIN  
3.- SOURCE  
4.- DRAIN

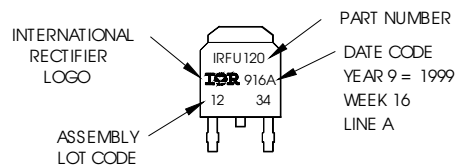
**IGBTs, CoPACK**

- 1.- GATE  
2.- COLLECTOR  
3.- EMITTER  
4.- COLLECTOR

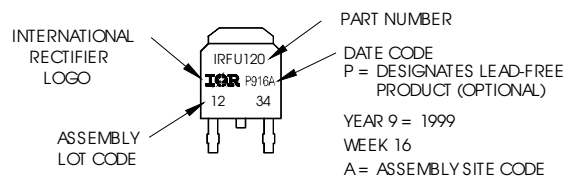
## D-Pak (TO-252AA) Part Marking Information

EXAMPLE: THIS IS AN IRFR120  
WITH ASSEMBLY  
LOT CODE 1234  
ASSEMBLED ON WW 16, 1999  
IN THE ASSEMBLY LINE "A"

Note: "P" in assembly line position  
indicates "Lead-Free"



OR



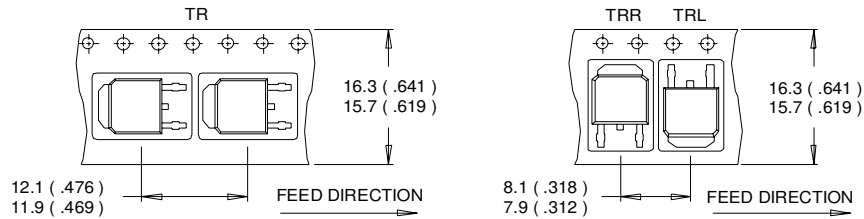


# IRFR/U3706

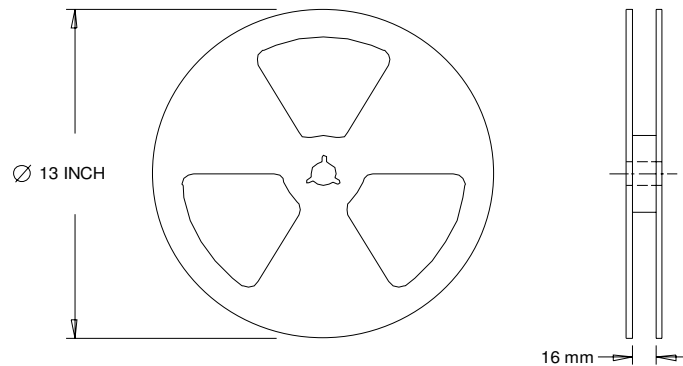
International  
**IR** Rectifier

## D-Pak (TO-252AA) Tape & Reel Information

Dimensions are shown in millimeters (inches)



- NOTES :
1. CONTROLLING DIMENSION : MILLIMETER.
  2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS ( INCHES ).
  3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



- NOTES :
1. OUTLINE CONFORMS TO EIA-481.

### Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting  $T_J = 25^\circ\text{C}$ ,  $L = 0.54\text{mH}$   
 $R_G = 25\Omega$ ,  $I_{AS} = 28\text{A}$ .
- ③ Pulse width  $\leq 400\mu\text{s}$ ; duty cycle  $\leq 2\%$ .
- ④ Calculated continuous current based on maximum allowable junction temperature. Package limitation current is 30A.
- ⑤  $R_\theta$  is measured at  $T_J$  approximately  $90^\circ\text{C}$

Data and specifications subject to change without notice.  
This product has been designed and qualified for the Industrial market.  
Qualification Standards can be found on IR's Web site.

International  
**IR** Rectifier

**IR WORLD HEADQUARTERS:** 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105  
TAC Fax: (310) 252-7903

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Note: For the most current drawings please refer to the IR website at:  
<http://www.irf.com/package/>